

SLV123TK

100V N-Channel MOSFET

General Description

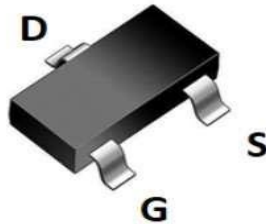
This Power MOSFET is produced using Maple semi's advanced planar stripeTRENCH technology. This advanced technology has been especially tailored to minimize conduction loss, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

Application

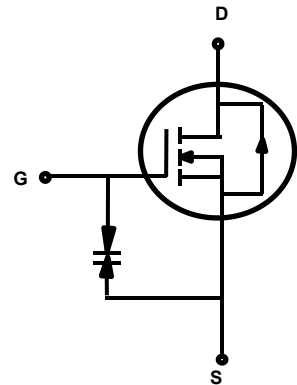
- Battery Protection
- Load Switch
- Power Management

Features

- N-Channel: 100V 0.17A
 $R_{DS(on)Typ} = 4\Omega @ V_{GS} = 10V$
 $R_{DS(on)Typ} = 6\Omega @ V_{GS} = 10V$
- Very Low On-resistance RDS(ON)
- LowCrss
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



SOT-23



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	SLV123TK	Units
V _{DSS}	Drain-Source Voltage	100	V
I _D	Drain Current - Continuous (T _C = 25°C)	0.17	A
	- Continuous (T _C = 100°C)	0.11	A
I _{DM}	Drain Current - Pulsed (Note 1)	0.68	A
V _{GSS}	Gate-Source Voltage	±20	V
P _D	Power Dissipation (T _C = 25°C)	35	W
R _{θJC}	Thermal Resistance, Junction to Case	357	°C/W
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C

* Drain current limited by maximum junction temperature.

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
--------	-----------	-----------------	-----	-----	-----	-------

Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	100	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$	--	--	10	μA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$	--	--	-10	μA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.5	2	2.5	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 0.5\text{ A}$	--	4	6	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 0.5\text{ A}$	--	6	9	Ω

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	60	-	pF
C_{oss}	Output Capacitance		--	15	-	pF
C_{rss}	Reverse Transfer Capacitance		--	6	-	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{GS} = 10\text{ V}, V_{DS} = 30\text{ V},$ $R_G = 50\text{ }\Omega, I_D = 0.1\text{ A}$	--	8	--	ns
t_r	Turn-On Rise Time		--	8	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	13	--	ns
t_f	Turn-Off Fall Time		--	6	--	ns
Q_g	Total Gate Charge	$V_{DS} = 30\text{ V}, I_D = 0.2\text{ A},$ $V_{GS} = 10\text{ V}$	--	2	--	nC
Q_{gs}	Gate-Source Charge		--	0.25	--	nC
Q_{gd}	Gate-Drain Charge		--	0.4	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	0.17	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	0.68	A
V_{SD}	Drain to Source Diode Forward Voltage, $V_{GS} = 0\text{ V}, I_{SD} = 0.2\text{ A}, T_J = 25^\circ\text{C}$	--	--	1.2	V

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$

N- Channel Typical Characteristics

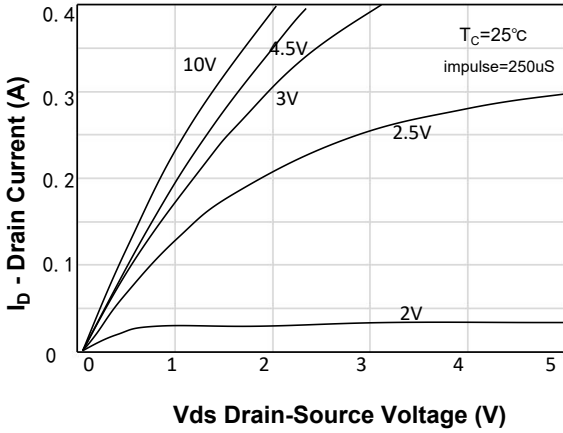


Figure 1. On-Region Characteristics

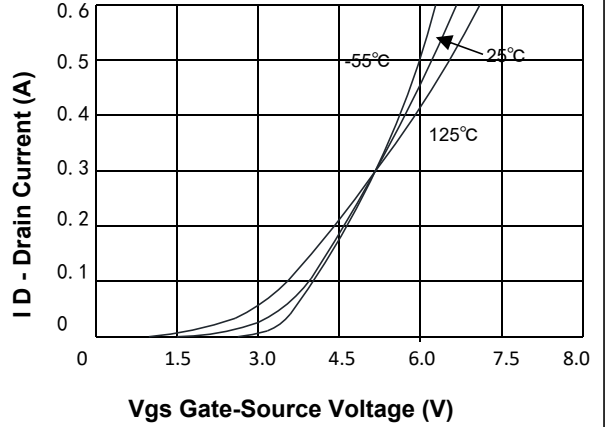


Figure 2. Transfer Characteristics

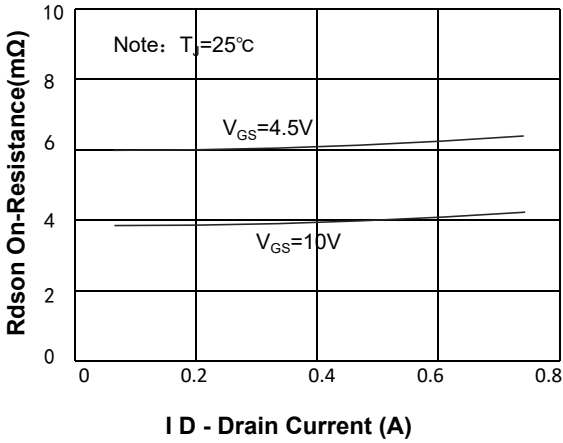


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

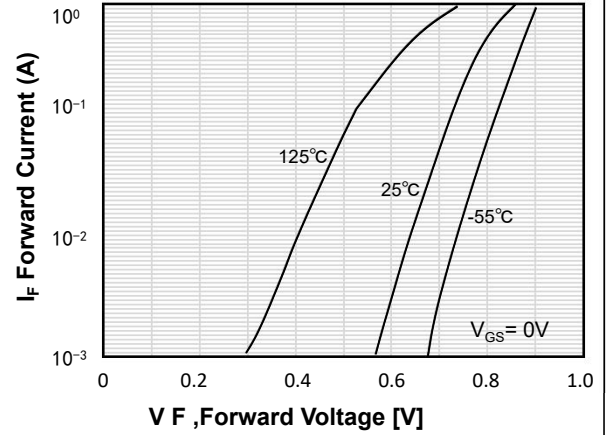


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

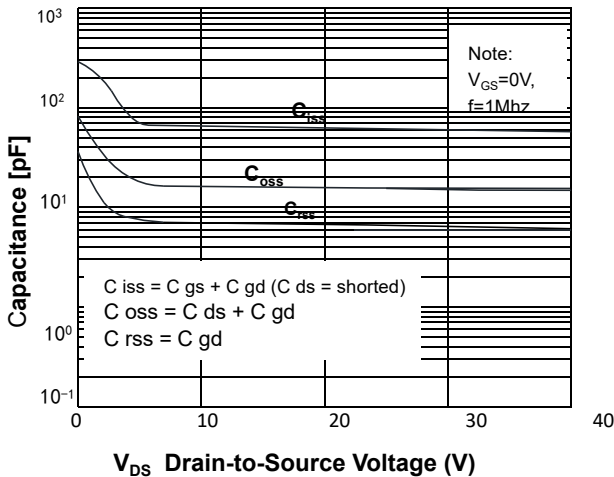


Figure 5. Capacitance Characteristics

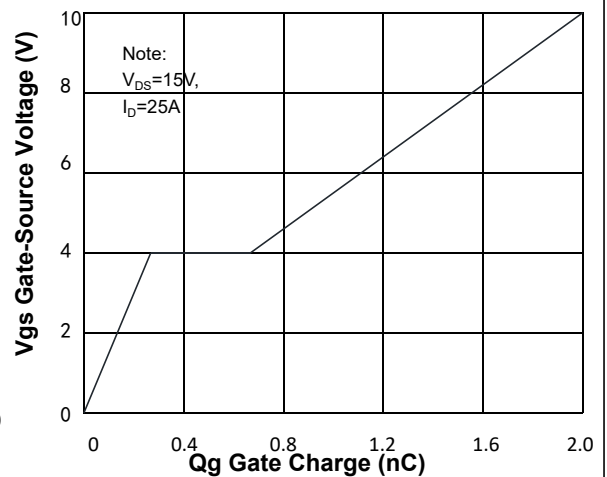


Figure 6. Gate Charge Characteristics

N- Channel Typical Characteristics (Continued)

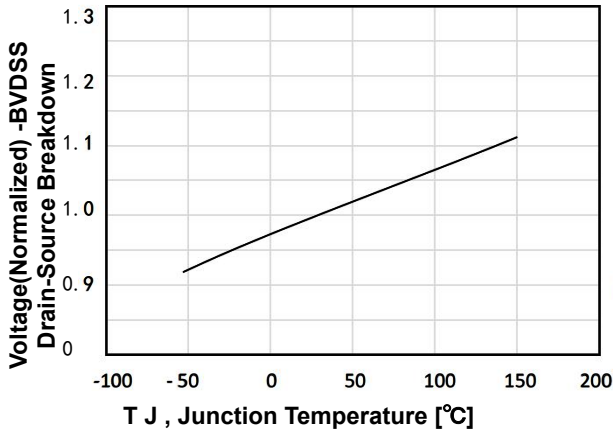


Figure 7. Breakdown Voltage Variation vs Temperature

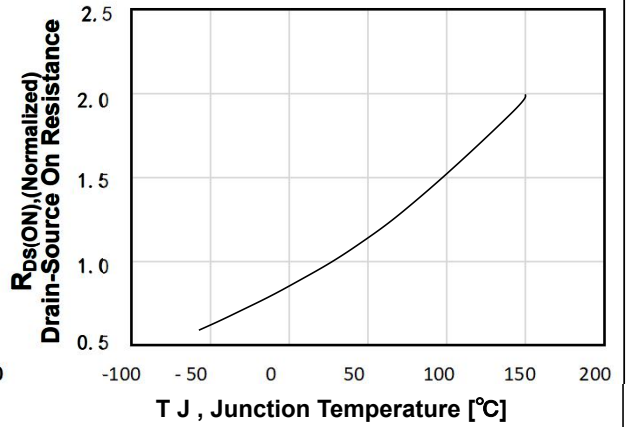


Figure 8. On-Resistance Variation vs Temperature

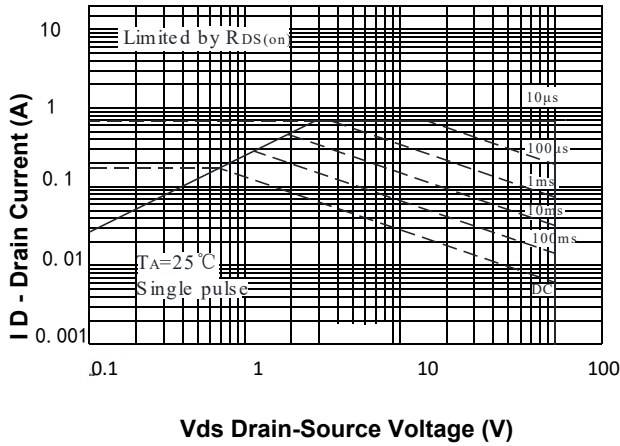


Figure 9. Maximum Safe Operating Area

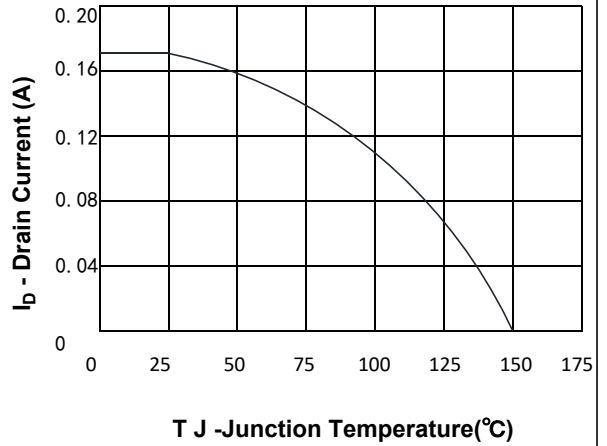


Figure 10. Maximum PContinuous Drain Current vs Case Temperature

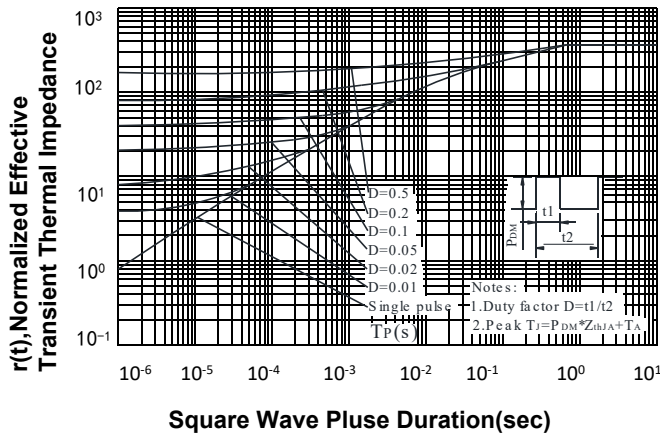
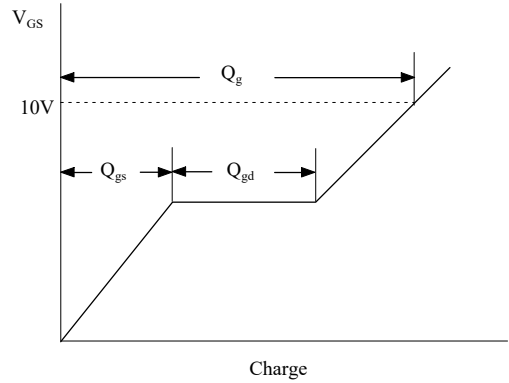
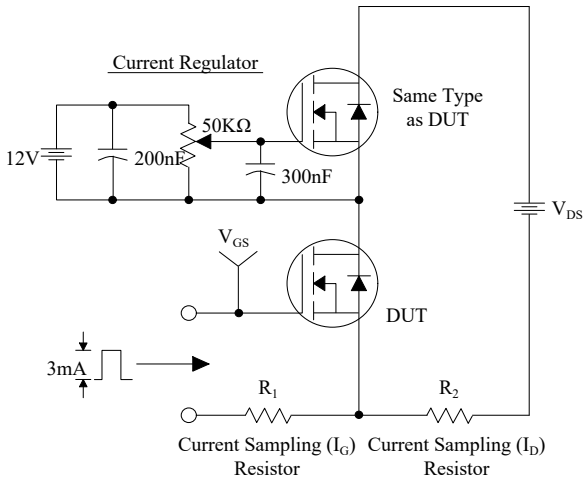
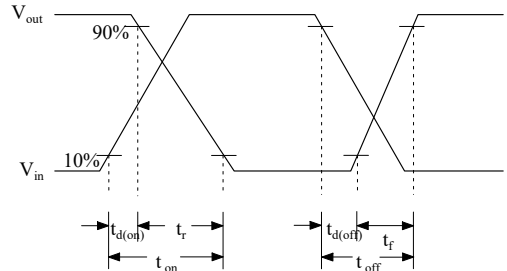
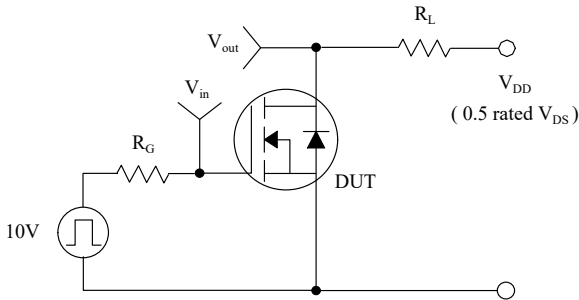


Figure 11. Transient Thermal Response Curve

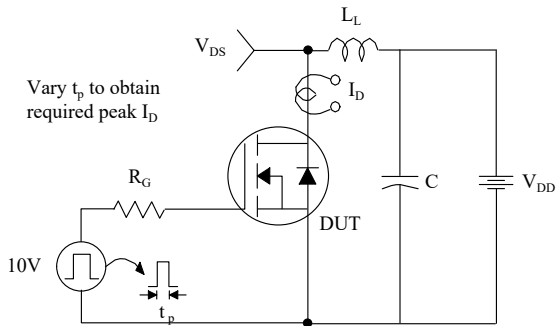
Gate Charge Test Circuit & Waveform



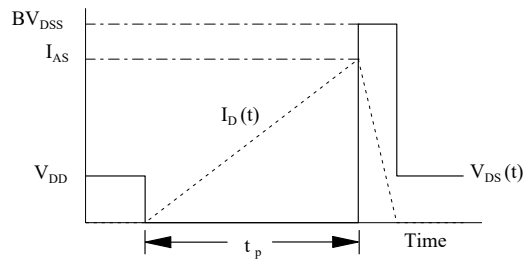
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



$$E_{AS} = \frac{1}{2} L_L I_{AS}^2$$



Peak Diode Recovery dv/dt Test Circuit & Waveforms

